24 DGND

23 REFB

22 REFBS

21 AGND

20 AGND

18 V_{DDA}

17 REFT

15 VDDA

14 🛮 V_{DDA}

13 V_{DDD}

16 REFTS

19 ANALOG IN

PW OR NS PACKAGE

(TOP VIEW)



8-BIT HIGH-SPEED ANALOG-TO-DIGITAL CONVERTER

features

- 8-Bit Resolution
- Differential Linearity Error
 - \pm 0.3 LSB Typ, \pm 1 LSB Max (25°C)
 - ±1 LSB Max
- Integral Linearity Error
 - \pm 0.6 LSB, \pm 0.75 LSB Max (25°C)
 - ±1 LSB Max
- Maximum Conversion Rate of 40 Megasamples Per Second (MSPS) Max
- Internal Sample and Hold Function
- 5-V Single Supply Operation
- Low Power Consumption . . . 85 mW Typ
- Analog Input Bandwidth . . . ≥75 MHz Typ
- Internal Reference Voltage Generators

applications

- Quadrature Amplitude Modulation (QAM) and Quadrature Phase Shift Keying (QPSK) Demodulators
- Digital Television
- Charge-Coupled Device (CCD) Scanners
- Video Conferencing
- Digital Set-Top Box
- Digital Down Converters
- High-Speed Digital Signal Processor Front End

CLK 12

D8(MSB) [] 10

V_{DDD} [] 11

OE

DGND [] 2

D2 🛮 4

D3 🛮 5

D4 **1** 6

D5 **1** 7

D6 **∏** 8

D7 **∏** 9

AVAILABLE OPTIONS

_	PACKAGE						
TA	TSSOP (PW)	SOP (NS)					
−0°C to 70°C	TLC5540CPW	TLC5540CNSLE					
-40°C to 85°C	TLC5540IPW	TLC5540INSLE					

description

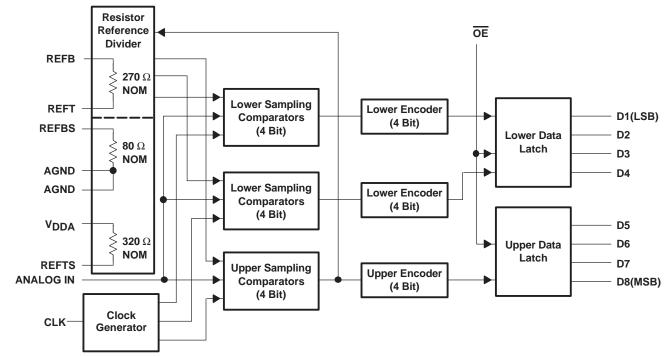
The TLC5540 is a high-speed, 8-bit analog-to-digital converter (ADC) that converts at sampling rates up to 40 megasamples per second (MSPS). Using a semiflash architecture and CMOS process, the TLC5540 is able to convert at high speeds while still maintaining low power consumption and cost. The analog input bandwidth of 75 MHz (typ) makes this device an excellent choice for undersampling applications. Internal resistors are provided to generate 2-V full-scale reference voltages from a 5-V supply, thereby reducing external components. The digital outputs can be placed in a high impedance mode. The TLC5540 requires only a single 5-V supply for operation.



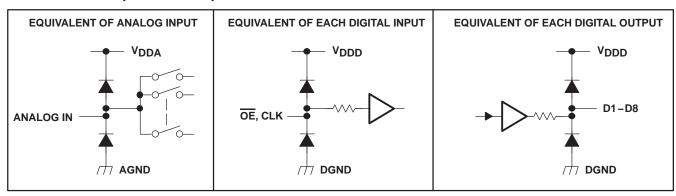
Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



functional block diagram



schematics of inputs and outputs





Terminal Functions

TERM	INAL		
NAME	NO.	1/0	DESCRIPTION
AGND	20, 21		Analog ground
ANALOG IN	19	I	Analog input
CLK	12	I	Clock input
DGND	2, 24		Digital ground
D1-D8	3-10	0	Digital data out. D1:LSB, D8:MSB
ŌĒ	1	- 1	Output enable. When \overline{OE} = L, data is enabled. When \overline{OE} = H, D1–D8 is high impedance.
V _{DDA}	14, 15, 18		Analog V _{DD}
V_{DDD}	11, 13		Digital V _{DD}
REFB	23	- 1	ADC reference voltage in (bottom)
REFBS	22		Reference voltage (bottom). When using the internal voltage divider to generate a nominal 2-V reference, the REFBS terminal is shorted to the REFB terminal and the REFTS terminal is shorted to the REFT terminal (see Figure 13 and Figure 14).
REFT	17	- 1	Reference voltage in (top)
REFTS	16		Reference voltage (top). When using the internal voltage divider to generate a nominal 2-V reference, the REFTS terminal is shorted to the REFT terminal and the REFBS terminal is shorted to the REFB terminal (see Figure 13 and Figure 14).

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage, V _{DDA} , V _{DDD}	7 V
Reference voltage input range, V _{I(REFT)} , V _{I(REFB)} , V _{I(REFBS)} , V _{I(REFTS)}	AGND to V _{DDA}
Analog input voltage range, V _{I(ANLG)}	
Digital input voltage range, V _{I(DGTL)}	
Digital output voltage range, VO(DGTL)	
Operating free-air temperature range, TA: TLC5540C	0°C to 70°C
TLC5540I	. -40°C to 85°C
Storage temperature range, T _{Stq}	-55°C to 150°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.



recommended operating conditions

			MIN	NOM	MAX	UNIT	
	V _{DDA} -AGND	V _{DDA} -AGND		5	5.25		
Supply voltage	V _{DDD} -AGND		4.75	5	5.25	V	
	AGND-DGND		-100	0	100	mV	
Reference input voltage (top), VI(REFT	·)		V _{I(REFB)} +1.8	V _{I(REFB)} +2	V_{DDA}	V	
Reference input voltage (bottom), VI(RI	EFB)		0	0.6	V _I (REFT)-1.8	V	
Analog input voltage range, V _{I(ANLG)} ((see Note 1)		VI(REFB)		V _I (REFT)		
Full scale voltage, VI(REFT) - VI(REFE	3)		1.8		5	V	
High-level input voltage, VIH	,		4			V	
Low-level input voltage, V _{IL}					1	V	
Pulse duration, clock high, t _W (H)			12.5			ns	
Pulse duration, clock low, t _{W(L)}			12.5			ns	
	TLC5540C	TLC5540C			70	°C	
Operating free-air temperature, T _A	TLC5540I		-40		85	°C	

^{(1) 1.8} V ≤ V_I(REFT) − V_I(REFB) < V_{DD}



electrical characteristics at V_{DD} = 5 V, $V_{I(REFT)}$ = 2.6 V, $V_{I(REFB)}$ = 0.6 V, f_{S} = 40 MSPS, T_{A} = 25°C (unless otherwise noted)

	PARAMETER	TES	ST CONDITIONS	t	MIN	TYP	MAX	UNIT
-	Linearity amon internal		T _A = 25°C		·	±0.6	±1	•
EL	Linearity error, integral	f _S = 40 MSPS,	T _A = MIN to MA	ıΧ			±1	1.00
-	Paradharman Manadhal	$V_I = 0.6 \text{ V to } 2.6 \text{ V}$	T _A = 25°C			±0.3	±0.75	LSB
ED	Linearity error, differential		$T_A = MIN \text{ to } MA$	ıΧ			±1	
	Self bias (1), V _{RB}	Short REFB to REFBS	0 5		0.57	0.61	0.65	
	Self bias (1), V _{RT}	Short REFT to REFTS	See Figure 13		2.47	2.63	2.80	
	Self bias (2), V _{RB}	Short REFB to AGND	0 5 11			AGND		V
	Self bias (2), V _{RT}	Short REFT to REFTS	See Figure 14	2.18	2.29	2.4		
I _{ref}	Reference-voltage current	VI(REFT) - VI(REFB) =	2 V	5.2	7.5	12	mA	
R _{ref}	Reference-voltage resistor	Between REFT and REF	165	270	350	Ω		
C _i	Analog input capacitance	$V_{I(ANLG)} = 1.5 V + 0.07$		4		pF		
EZS	Zero-scale error					-43	-68	.,
E _{FS}	Full-scale error	V _I (REFT) - V _I (REFB) =	2 V		-25	0	25	mV
lн	High-level input current	V _{DD} = 5.25 V,	V _{IH} = V _{DD}				5	^
IIL	Low-level input current	V _{DD} = 5.25 V,	V _{IL} = 0				5	μΑ
ІОН	High-level output current	OE = GND,	$V_{DD} = 4.75 V$,	$V_{OH} = V_{DD} - 0.5 V$	-1.5			A
loL	Low-level output current	OE = GND,	$V_{DD} = 4.75 V$,	V _{OL} = 0.4 V	2.5			mA
IOZH(lkg)	High-level high-impedance-state output leakage current	$\overline{OE} = V_{DD}$,	V _{DD} = 5.25,	V _{OH} = V _{DD}			16	
IOZL(Ikg)	Low-level high-impedance-state output leakage current	$\overline{OE} = V_{DD}$,	V _{DD} = 4.75,	V _{OL} = 0			16	μА
I _{DD}	Supply current	$f_S = 40 \text{ MSPS}, C_L \le 25 \text{ pNTSC}^{\ddagger}$ ramp wave input				17	27	mA

[†]Conditions marked MIN or MAX are as stated in recommended operating conditions.

‡ National Television System Committee

(1) Supply current specification does not include I_{ref}.



operating characteristics at V_{DD} = 5 V, V_{RT} = 2.6 V, V_{RB} = 0.6 V, f_s = 40 MSPS, T_A = 25°C (unless otherwise noted)

	PARAMETER	TEST C	ONDITIONS†	MIN	TYP	MAX	UNIT	
f _S	Maximum conversion rate	$T_A = MIN \text{ to } MA$	λX	40			MSPS	
f _S	Minimum conversion rate	$T_A = MIN \text{ to } MA$	λX		5		MSPS	
BW	Analog input full-power bandwidth	At – 3 dB,	V _I (ANLG) = 2 V _{pp}		75		MHz	
t _{pd}	Delay time, digital output	C _L ≤ 10 pF (see	e Note 2)		9	15	ns	
tPHZ	Disable time, output high to Hi-Z	C _L ≤ 15 pF,	$I_{OH} = -4.5 \text{ mA}$			20	ns	
tPLZ	Disable time, output low to Hi-Z	C _L ≤ 15 pF,	I _{OL} = 5 mA			20	ns	
^t PZH	Enable time, Hi-Z to output high	C _L ≤ 15 pF,	$I_{OH} = -4.5 \text{ mA}$			15	ns	
tPZL	Enable time, Hi-Z to output low	C _L ≤ 15 pF,	I _{OL} = 5 mA			15	ns	
	Differential gain	NTSC 40 IRE‡	modulation wave,		1%			
	Differential phase	f _S = 14.3 MSPS			0.7		degrees	
t _A J	Aperture jitter time				30		ps	
t _{d(s)}	Sampling delay time				4		ns	
			f _I = 1 MHz		47		dB	
		,	f _I = 3 MHz	44	47			
		$f_S = 20 \text{ MSPS}$	f _I = 6 MHz		46			
SNR	Signal-to-noise ratio		f _I = 10 MHz		45			
			f _I = 3 MHz		45.2			
		f _S = 40 MSPS	f _I = 6 MHz	42	44			
			f _I = 10 MHz		42			
			f _I = 1 MHz		7.64			
		(00 140 00	f _I = 3 MHz	7.61			1	
ENOD	Effective acceptance of hits	$f_S = 20 \text{ MSPS}$	f _I = 6 MHz		7.47		D'i-	
ENOB	Effective number of bits		f _I = 10 MHz		7.16		Bits	
		4 40 MCDC	f _I = 3 MHz		7			
		f _S = 40 MSPS	f _I = 6 MHz		6.8			
			f _I = 1 MHz		43			
		£ 20 MCDC	f _I = 3 MHz	35	42			
TUD	Total harmania diatartian	$f_S = 20 \text{ MSPS}$	f _I = 6 MHz		41		dBc	
THD	Total harmonic distortion		f _I = 10 MHz		38			
		f _ 40 Mene	f _I = 3 MHz		40			
		f _S = 40 MSPS	f _I = 6 MHz		38			
	Spurious froe dynamic ronge	f _S = 20 MSPS	f _S = 20 MSPS		46		dBo	
	Spurious-free dynamic range	$f_S = 40 \text{ MSPS}$	f _I = 3 MHz		42		dBc	

[†] Conditions marked MIN or MAX are as stated in recommended operating conditions.

‡ Institute of Radio Engineers

(2) C_L includes probe and jig capacitance.



PARAMETER MEASUREMENT INFORMATION

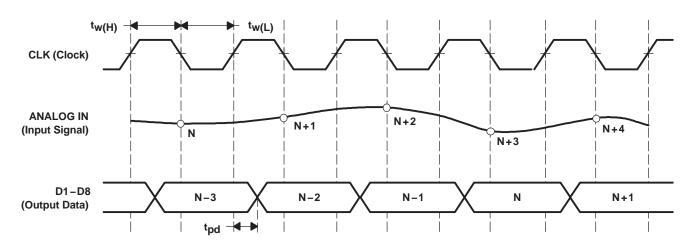


Figure 1. I/O Timing Diagram

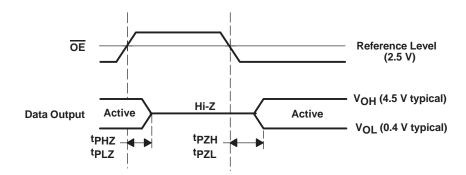


Figure 2. I/O Timing Diagram



TYPICAL CHARACTERISTICS

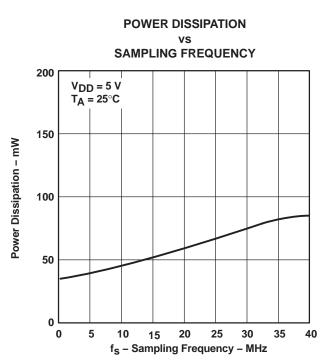
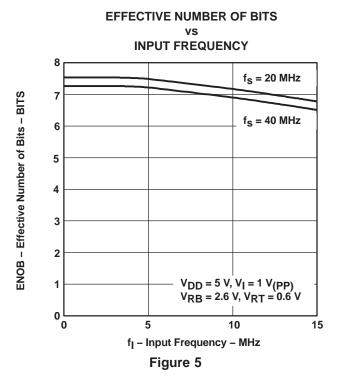


Figure 3



ANALOG INPUT BANDWIDTH 0.5 0 -0.5 -1.5 Gain - dB -2.5 -3 -3.5 V_{CC} = 5 V, V_{RT} = 2.6 V, V_{RB} = 0.6 V CLK = 40 MHz ANALOG IN = 100 k - 100 MHz Sine Wave -4.5 $V_I = 2 V_{(PP)}$ -5∟ 0.1 100 10 f_I - Input Frequency - MHz

Figure 4

SIGNAL-TO-NOISE RATIO

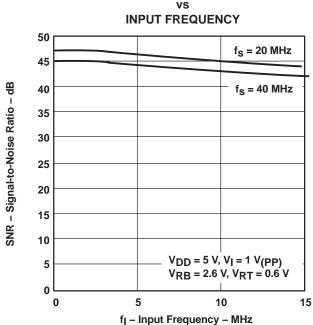


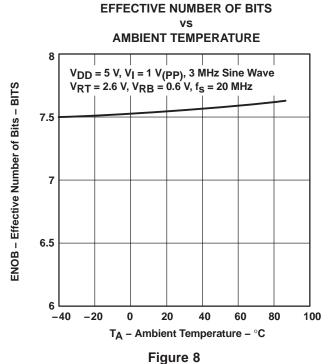
Figure 6

8

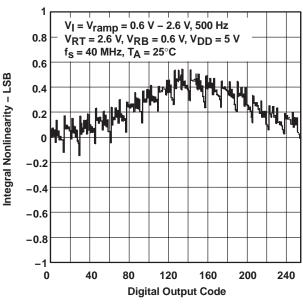


TYPICAL CHARACTERISTICS

DIFFERENTIAL NONLINEARITY $V_I = V_{ramp} = 0.6 V - 2.6 V, 500 Hz$ 0.8 V_{RT} = 2.6 V, V_{RB} = 0.6 V, V_{DD} = 5 V f_S = 40 MHz 0.6 T_A = 25°C Differential Nonlinearity - LSB 0.4 0.2 0 -0.2 -0.4-0.6 -0.80 40 80 120 160 200 240 **Digital Output Code** Figure 7



INTEGRAL NONLINEARITY



FFT SPECTRUM

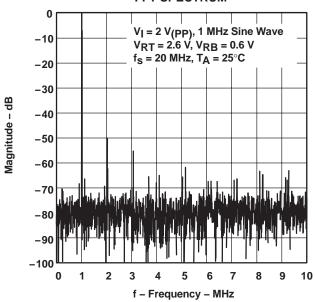


Figure 9

Figure 10



APPLICATION INFORMATION

grounding and power supply considerations

A signal ground is a low-impedance path for current to return to the source. Inside the TLC5540 A/D converter, the analog ground and digital ground are connected to each other through the substrate, which has a very small resistance (\sim 30 Ω) to prevent internal latch-up. For this reason, it is strongly recommended that a printed circuit board (PCB) of at least 4 layers be used with the TLC5540 and the converter DGND and AGND pins be connected directly to the analog ground plane to avoid a ground loop. Figure 11 shows the recommended decoupling and grounding scheme for laying out a multilayer PC board with the TLC5540. This scheme ensures that the impedance connection between AGND and DGND is minimized so that their potential difference is negligible and noise source caused by digital switching current is eliminated.

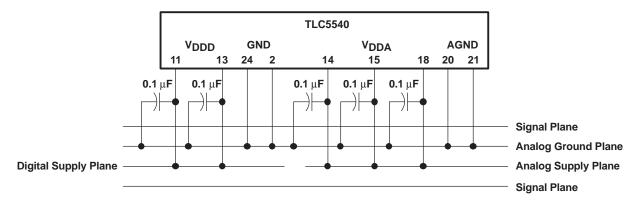


Figure 11. AV_{DD}, DV_{DD}, AGND, and DGND Connections

printed circuit board (PCB) layout considerations

When designing a circuit that includes high-speed digital and precision analog signals such as a high speed ADC, PCB layout is a key component to achieving the desired performance. The following recommendations should be considered during the prototyping and PCB design phase:

- Separate analog and digital circuitry physically to help eliminate capacitive coupling and crosstalk. When separate analog and digital ground planes are used, the digital ground and power planes should be several layers from the analog signals and power plane to avoid capacitive coupling.
- Full ground planes should be used. Do not use individual etches to return analog and digital currents or partial ground planes. For prototyping, breadboards should be constructed with copper clad boards to maximize ground plane.
- The conversion clock, CLK, should be terminated properly to reduce overshoot and ringing. Any jitter on the conversion clock degrades ADC performance. A high-speed CMOS buffer such as a 74ACT04 or 74AC04 positioned close to the CLK terminal can improve performance.
- Minimize all etch runs as much as possible by placing components very close together. It also proves beneficial to place the ADC in a corner of the PCB nearest to the I/O connector analog terminals.
- It is recommended to place the digital output data latch (if used) as close to the TLC5540 as possible to minimize capacitive loading. If D0 through D7 must drive large capacitive loads, internal ADC noise may be experienced.



functional description

The TLC5540 uses a modified semiflash architecture as shown in the functional block diagram. The four most significant bits (MSBs) of every output conversion result are produced by the upper comparator block CB1. The four least significant bits (LSBs) of each alternate output conversion result are produced by the lower comparator blocks CB-A and CB-B in turn (see Figure 12).

The reference voltage that is applied to the lower comparator resistor string is one sixteenth of the amplitude of the refence applied to the upper comparator resistor string. The sampling comparators of the lower comparator block require more time to sample the lower voltages of the reference and residual input voltage. By applying the residual input voltage to alternate lower comparator blocks, each comparator block has twice as much time to sample and convert as would be the case if only one lower comparator block were used.

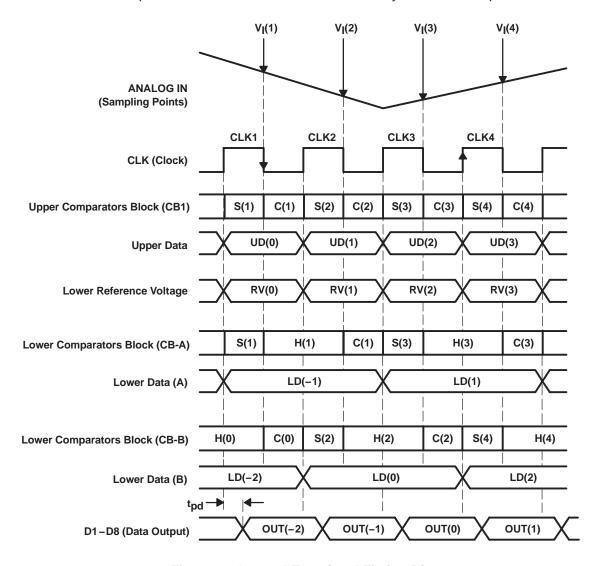


Figure 12. Internal Functional Timing Diagram

This conversion scheme, which reduces the required sampling comparators by 30 percent compared to standard semiflash architectures, achieves significantly higher sample rates than the conventional semiflash conversion method.



functional description (continued)

The MSB comparator block converts on the falling edge of each applied clock cycle. The LSB comparator blocks CB-A and CB-B convert on the falling edges of the first and second following clock cycles, respectively. The timing diagram of the conversion algorithm is shown in Figure 12.

analog input operation

The analog input stage to the TLC5540 is a chopper-stabilized comparator and is equivalently shown below:

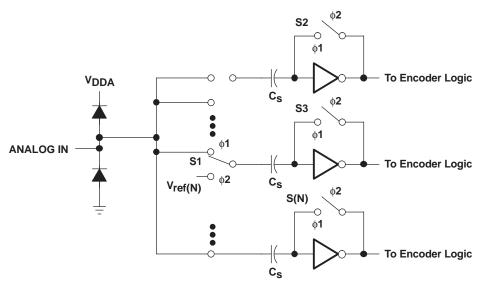


Figure 13. External Connections for Using the Internal Reference Resistor Divider

Figure 13 depicts the analog input for the TLC5540. The switches shown are controlled by two internal clocks, $\phi 1$ and $\phi 2$. These are nonoverlapping clocks that are generated from the CLK input. During the sampling period, $\phi 1$, S1 is closed and the input signal is applied to one side of the sampling capacitor, C_S . Also during the sampling period, S2 through S(N) are closed. This sets the comparator input to approximately 2.5 V. The delta voltage is developed across C_S . During the comparison phase, $\phi 2$, S1 is switched to the appropriate reference voltage for the bit value N. S2 is opened and $V_{ref(N)} - VC_S$ toggles the comparator output to the appropriate digital 1 or 0. The small resistance values for the switch, S1, and small value of the sampling capacitor combine to produce the wide analog input bandwidth of the TLC5540. The source impedance driving the analog input of the TLC5540 should be less than 100 Ω across the range of input frequency spectrum.

reference inputs – REFB, REFT, REFBS, REFTS

The range of analog inputs that can be converted are determined by REFB and REFT, REFT being the maximum reference voltage and REFB being the minimum reference voltage. The TLC5540 is tested with REFT = 2.6 V and REFB = 0.6 V producing a 2-V full-scale range. The TLC5540 can operate with REFT – REFB = 5 V, but the power dissipation in the reference resistor increases significantly (93 mW nominally). It is recommended that a 0.1 μF capacitor be attached to REFB and REFT whether using externally or internally generated voltages.



internal reference voltage conversion

Three internal resistors allow the device to generate an internal reference voltage. These resistors are brought out on terminals V_{DDA} , REFTS, REFB, REFBS, and AGND. Two different bias voltages are possible without the use of external resistors.

Internal resistors are provided to develop REFT = 2.6 V and REFB = 0.6 V (bias option one) with only two external connections. This is developed with a 3-resistor network connected to V_{DDA} . When using this feature, connect REFT to REFTS and connect REFB to REFBS. For applications where the variance associated with V_{DDA} is acceptable, this internal voltage reference saves space and cost (see Figure 14).

A second internal bias option (bias two option) is shown in Figure 15. Using this scheme REFB = AGND and REFT = 2.28 V nominal. These bias voltage options can be used to provide the values listed in the following table.

DIAG OPTION	BIAS VOLTAGE								
BIAS OPTION	V _{RB}	V _{RT}	V _{RT} – V _{RB}						
1	0.61	2.63	2.02						
2	AGND	2.28	2.28						

Table 1. Bias Voltage Options

To use the internally-generated reference voltage, terminal connections should be made as shown in Figure 14 or Figure 15. The connections in Figure 14 provide the standard video 2-V reference.

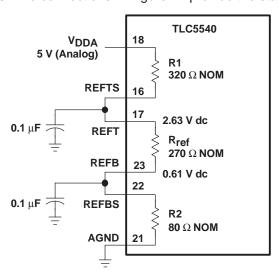


Figure 14. External Connections Using the Internal Bias One Option



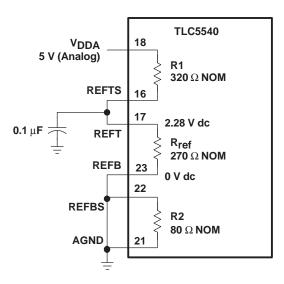


Figure 15. External Connections Using the Internal Bias Two Option

functional operation

Table 2 shows the TLC5540 functions.

Table 2. Functional Operation

INPUT SIGNAL	0750		DIGITAL OUTPUT CODE								
VOLTAGE	STEP	MSB	MSB								
V _{ref(T)}	255	1	1	1	1	1	1	1	1		
•	•	•	•	•	•	•	•	•	•		
•	•	•	•	•	•	•	•	•	•		
•	128	1	0	0	0	0	0	0	0		
•	127	0	1	1	1	1	1	1	1		
•	•	•	•	•	•	•	•	•	•		
•	•	•	•	•	•	•	•	•	•		
V _{ref(B)}	0	0	0	0	0	0	0	0	0		





10-Dec-2020

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
TLC5540CPW	ACTIVE	TSSOP	PW	24	60	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	0 to 70	P5540	Samples
TLC5540INSR	ACTIVE	SO	NS	24	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	TLC5540I	Samples
TLC5540IPW	ACTIVE	TSSOP	PW	24	60	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	Y5540	Samples
TLC5540IPWR	ACTIVE	TSSOP	PW	24	2000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	Y5540	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE OPTION ADDENDUM

10-Dec-2020

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PACKAGE MATERIALS INFORMATION

www.ti.com 5-Dec-2023

TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TLC5540INSR	so	NS	24	2000	330.0	24.4	8.5	15.3	2.6	12.0	24.0	Q1
TLC5540IPWR	TSSOP	PW	24	2000	330.0	16.4	6.95	8.3	1.6	8.0	16.0	Q1

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*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TLC5540INSR	SO	NS	24	2000	350.0	350.0	43.0
TLC5540IPWR	TSSOP	PW	24	2000	350.0	350.0	43.0

PACKAGE MATERIALS INFORMATION

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TUBE



*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
TLC5540CPW	PW	TSSOP	24	60	530	10.2	3600	3.5
TLC5540IPW	PW	TSSOP	24	60	530	10.2	3600	3.5





NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.





NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



MECHANICAL DATA

NS (R-PDSO-G**)

14-PINS SHOWN

PLASTIC SMALL-OUTLINE PACKAGE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15.







NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

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- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
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NOTES: (continued)

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NOTES: (continued)

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